

**30V N-CHANNEL ENHANCEMENT MODE MOSFET IN SOT23**

**Product Summary**

$V_{(BR)DSS}$	Max $R_{DS(on)}$	$I_D$ Max (Note 5) $T_A = 25^\circ C$
30V	460m $\Omega$ @ $V_{GS} = 4.5V$	0.94A
	560m $\Omega$ @ $V_{GS} = 2.5V$	0.85A

**Description and Applications**

This MOSFET has been designed to minimize the on-state resistance ( $R_{DS(on)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

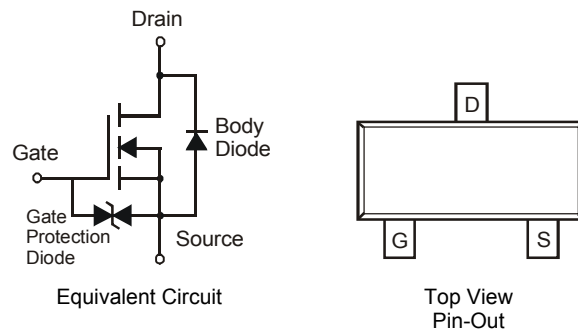
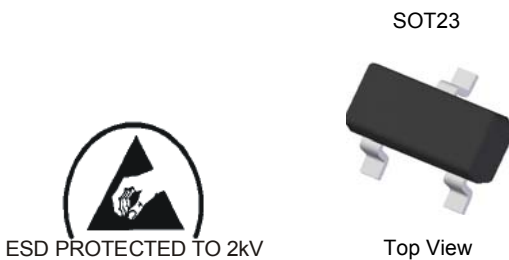
- Load switch
- Portable applications
- Power Management Functions

**Features and Benefits**

- Low  $V_{GS(th)}$ , can be driven directly from a battery
- Low  $R_{DS(on)}$
- "Lead Free", RoHS Compliant (Note 1)
- Halogen and Antimony Free. "Green" Device (Note 2)
- ESD Protected Gate 2kV
- Qualified to AEC-Q101 Standards for High Reliability

**Mechanical Data**

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish-Matte Tin.
- Weight: 0.08 grams (approximate)

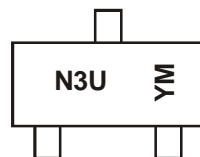


**Ordering Information** (Note 3)

Part Number	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
DMN3730U-7	N3U	7	8	3,000

- Notes:
1. No purposefully added lead
  2. Diodes Inc's "Green" policy can be found on our website at <http://www.diodes.com>.
  3. For packaging details, go to our website at <http://www.diodes.com>.

**Marking Information**



N3U = Product Type Marking Code  
 YM = Date Code Marking  
 Y = Year (ex: Y = 2011)  
 M = Month (ex: 9 = September)

Date Code Key

Year Code	2011	2012	2013	2014	2015	2016	2017
Code	Y	Z	A	B	C	D	E

Month Code	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

**Maximum Ratings** @ $T_A = 25^\circ\text{C}$  unless otherwise specified

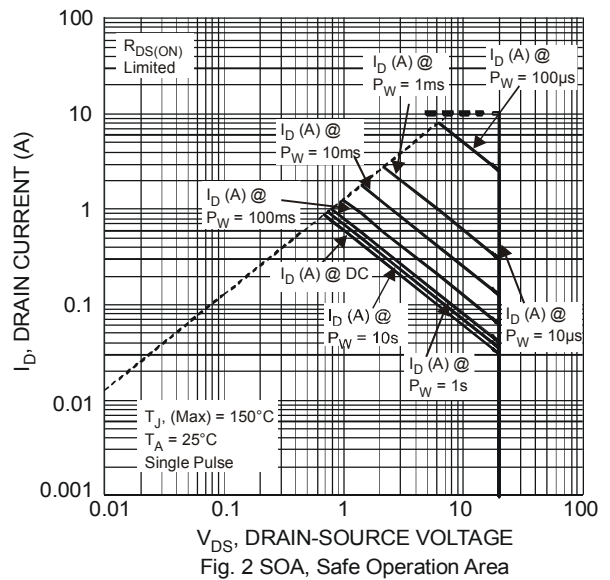
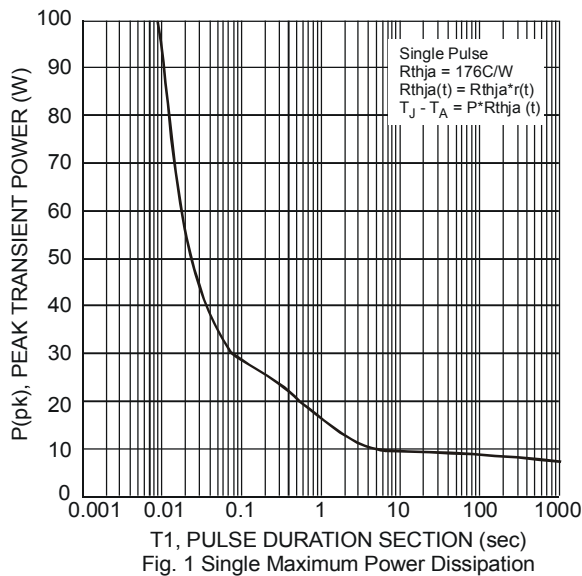
Characteristic			Symbol	Value	Unit
Drain-Source Voltage			$V_{DSS}$	30	V
Gate-Source Voltage			$V_{GSS}$	$\pm 8$	V
Continuous Drain Current	Steady State	$T_A = 25^\circ\text{C}$ (Note 5)	$I_D$	0.94	A
		$T_A = 85^\circ\text{C}$ (Note 5)		0.68	
		$T_A = 25^\circ\text{C}$ (Note 4)		0.75	
Pulsed Drain Current (Note 6)			$I_{DM}$	10	A

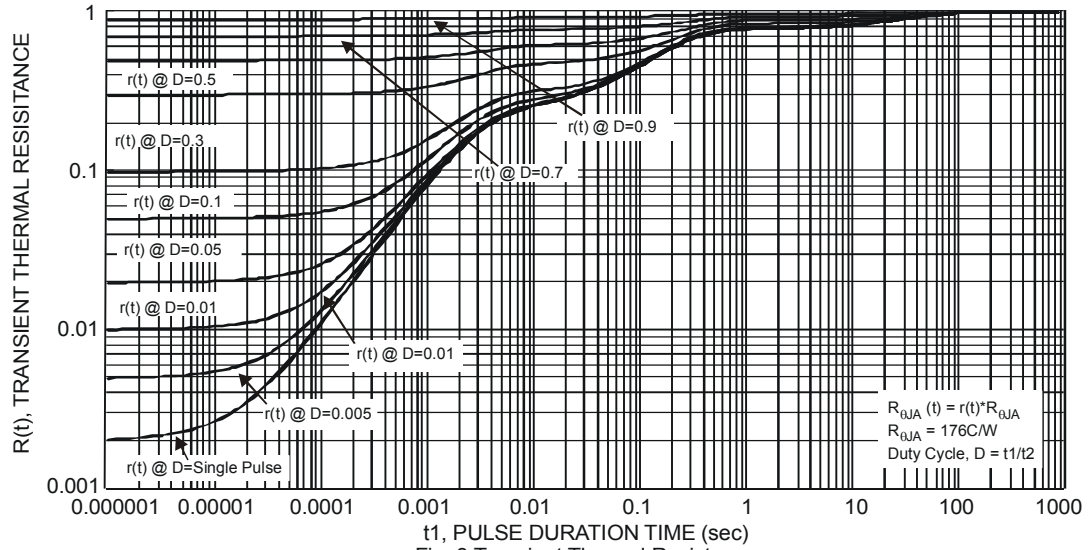
**Thermal Characteristics** @ $T_A = 25^\circ\text{C}$  unless otherwise specified

Characteristic		Symbol	Value	Unit
Power Dissipation	(Note 4)	$P_D$	0.45	W
	(Note 5)		0.71	W
Thermal Resistance, Junction to Ambient	(Note 4)	$R_{\theta JA}$	275	$^\circ\text{C/W}$
	(Note 5)		177	$^\circ\text{C/W}$
Operating and Storage Temperature Range		$T_J, T_{STG}$	-55 to +150	$^\circ\text{C}$

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout
  - Device mounted on 25mm X 25mm square copper plate with FR-4 substrate PC board, 2oz copper
  - Device mounted on minimum recommended pad layout test board, 10 $\mu\text{s}$  pulse duty cycle = 1%.

**Thermal Characteristics**





**Electrical Characteristics** @ $T_A = 25^\circ\text{C}$  unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	30	-	-	V	$V_{GS} = 0V, I_D = 10\mu A$
Zero Gate Voltage Drain Current	$I_{DSS}$	-	-	1	$\mu A$	$V_{DS} = 30V, V_{GS} = 0V$
Gate-Source Leakage	$I_{GSS}$	-	-	3	$\mu A$	$V_{GS} = \pm 8V, V_{DS} = 0V$
<b>ON CHARACTERISTICS</b>						
Gate Threshold Voltage	$V_{GS(th)}$	0.45	-	0.95	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
Static Drain-Source On-Resistance (Note 7)	$R_{DS(on)}$	-	-	460	m $\Omega$	$V_{GS} = 4.5V, I_D = 200mA$
				560		$V_{GS} = 2.5V, I_D = 100mA$
				730		$V_{GS} = 1.8V, I_D = 75mA$
Forward Transfer Admittance	$ Y_{fs} $	40	-	-	mS	$V_{DS} = 3V, I_D = 10mA$
Diode Forward Voltage (Note 7)	$V_{SD}$	-	0.7	1.2	V	$V_{GS} = 0V, I_S = 300mA$
<b>DYNAMIC CHARACTERISTICS (Note 8)</b>						
Input Capacitance	$C_{iss}$	-	64.3	-	pF	$V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz$
Output Capacitance	$C_{oss}$	-	6.1	-	pF	
Reverse Transfer Capacitance	$C_{rss}$	-	4.5	-	pF	
Gate Resistance	$R_g$	-	70	-	$\Omega$	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$
Total Gate Charge	$Q_g$	-	1.6	-	nC	$V_{GS} = 4.5V, V_{DS} = 15V, I_D = 1A$
Gate-Source Charge	$Q_{gs}$	-	0.2	-	nC	
Gate-Drain Charge	$Q_{gd}$	-	0.2	-	nC	
Turn-On Delay Time	$t_{D(on)}$	-	3.5	-	ns	$V_{DS} = 10V, I_D = 1A, V_{GS} = 10V, R_G = 6\Omega$
Turn-On Rise Time	$t_r$	-	2.8	-	ns	
Turn-Off Delay Time	$t_{D(off)}$	-	38	-	ns	
Turn-Off Fall Time	$t_f$	-	13	-	ns	

Notes: 7. Measured under pulsed conditions to minimize self-heating effect. Pulse width  $\leq 300\mu s$ ; duty cycle  $\leq 2\%$   
8. For design aid only, not subject to production testing.

**DMN3730U**

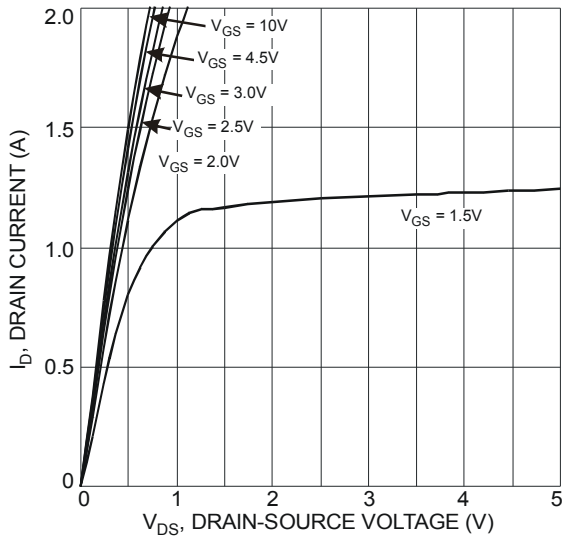


Fig. 4 Typical Output Characteristic

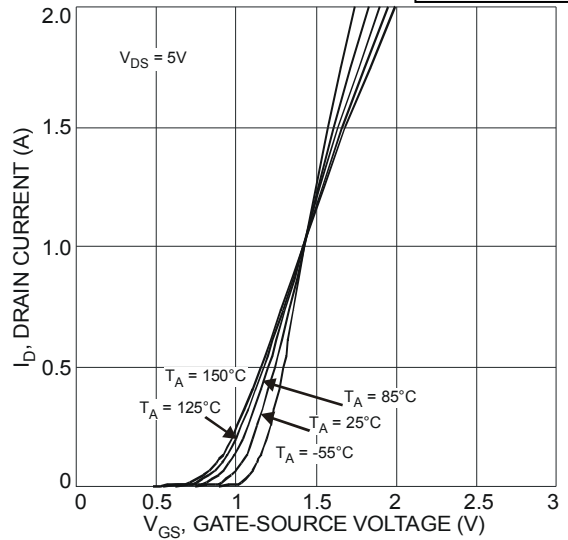


Fig. 5 Typical Transfer Characteristic

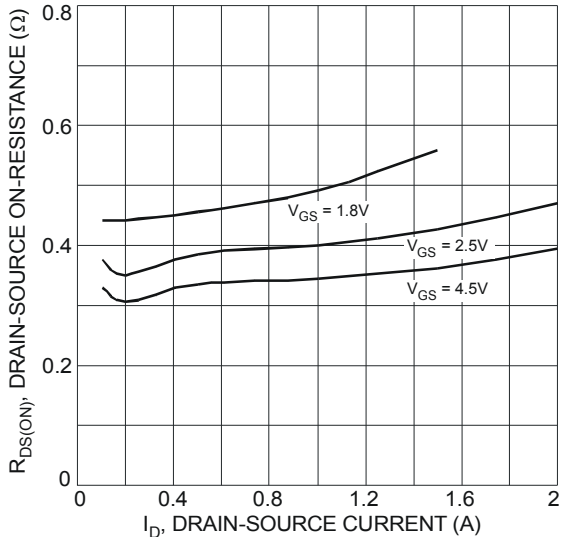


Fig. 6 Typical On-Resistance vs. Drain Current and Gate Voltage

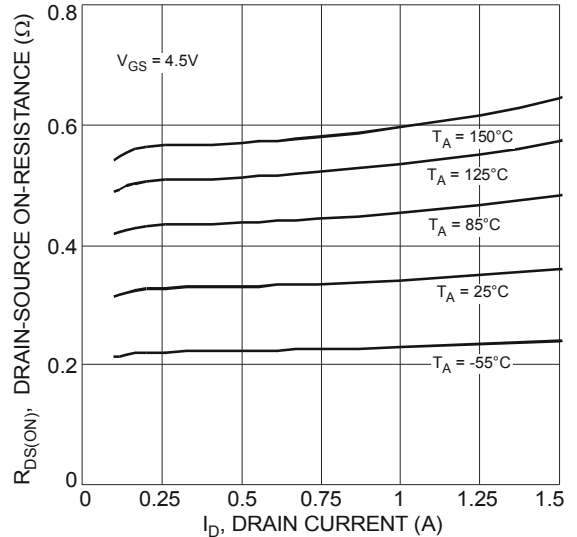


Fig. 7 Typical On-Resistance vs. Drain Current and Temperature

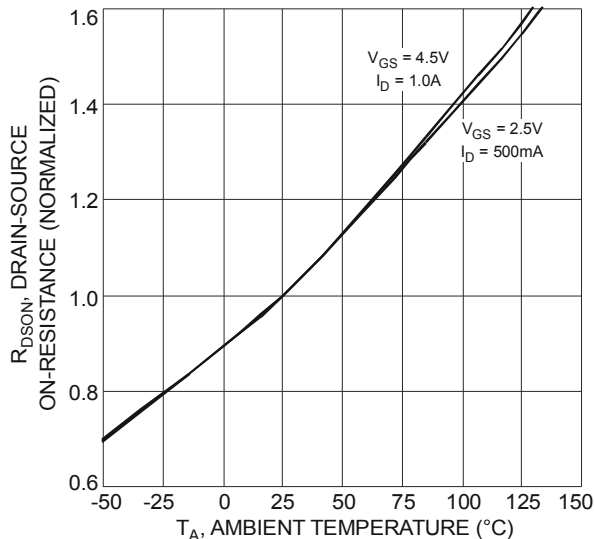


Fig. 8 On-Resistance Variation with Temperature

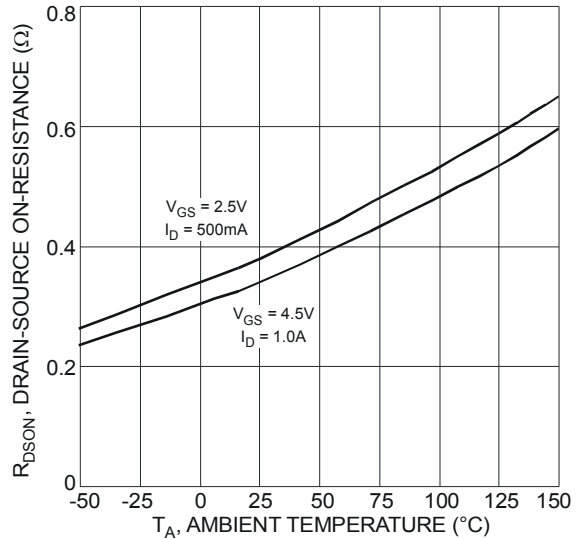


Fig. 9 On-Resistance Variation with Temperature

**DMN3730U**

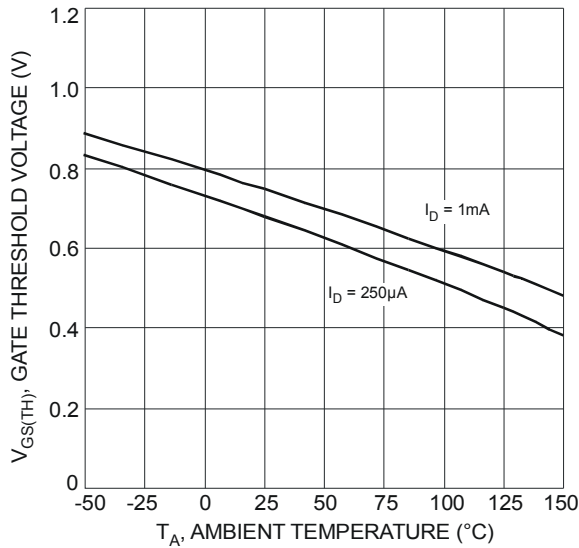


Fig. 10 Gate Threshold Variation vs. Ambient Temperature

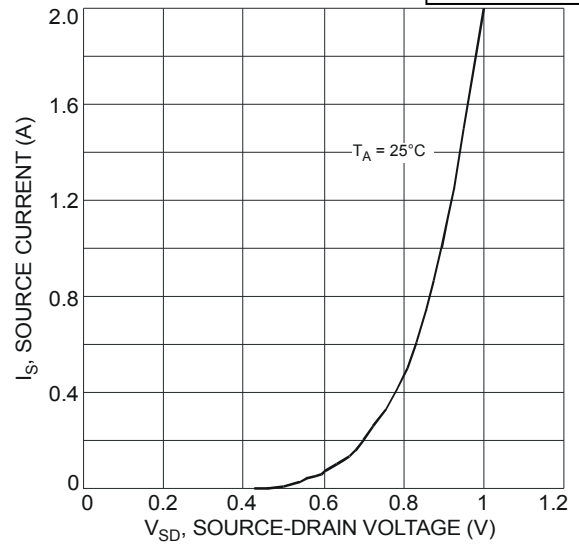


Fig. 11 Diode Forward Voltage vs. Current

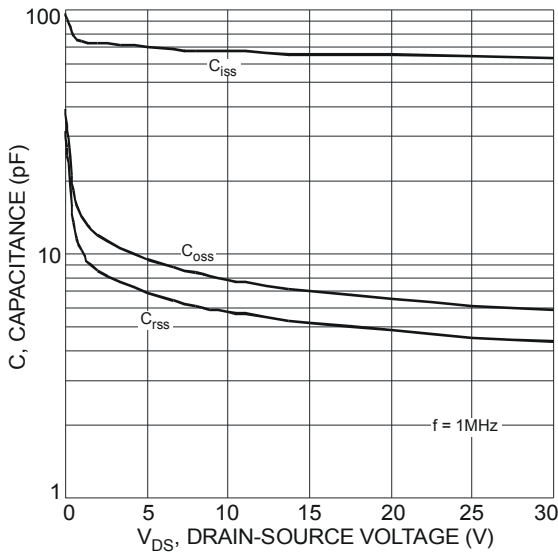


Fig. 12 Typical Total Capacitance

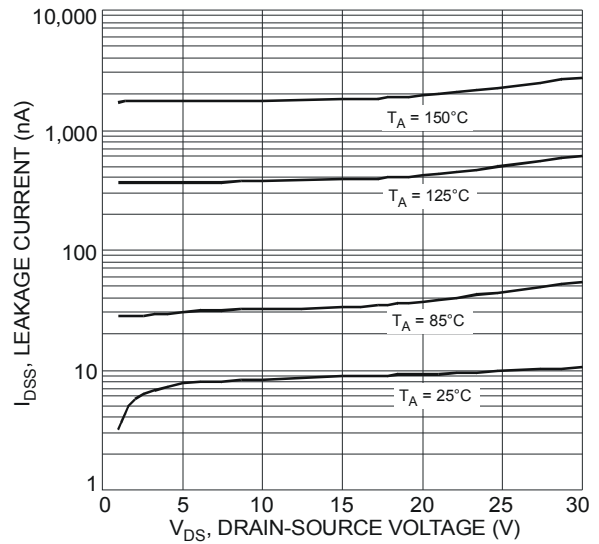


Fig. 13 Typical Leakage Current vs. Drain-Source Voltage

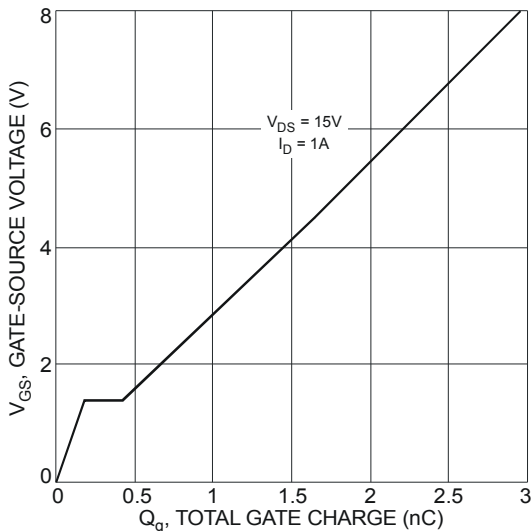
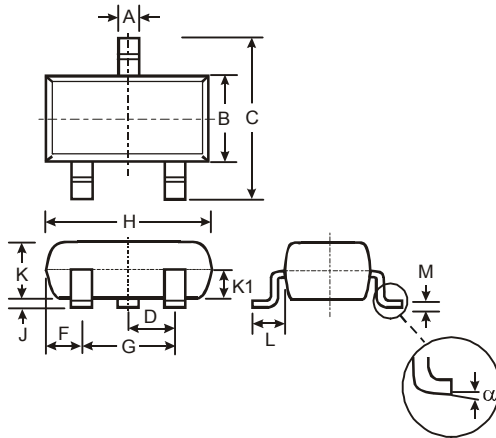


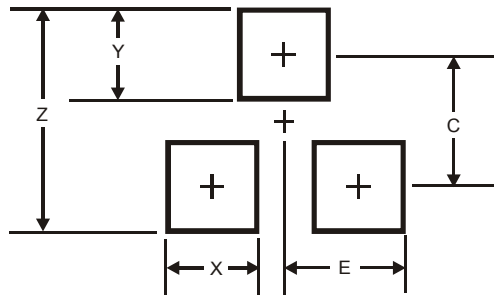
Fig. 14 Gate-Charge Characteristics

**Package Outline Dimensions**



SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.903	1.10	1.00
K1	-	-	0.400
L	0.45	0.61	0.55
M	0.085	0.18	0.11
α	0°	8°	-
All Dimensions in mm			

**Suggested Pad Layout**



Dimensions	Value (in mm)
Z	2.9
X	0.8
Y	0.9
C	2.0
E	1.35

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